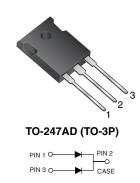


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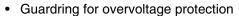
# **Dual Common-Cathode Schottky Rectifier**

High Barrier Technology for Improved High Temperature Performance



PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub>	40 A					
V <sub>RRM</sub>	35 V to 60 V					
I <sub>FSM</sub>	400 A					
V <sub>F</sub>	0.55 V, 0.60 V					
T <sub>J</sub> max.	175 °C					

### **FEATURES**





- · Lower power losses, high efficiency
- · Low forward voltage drop
- · High forward surge capability
- · High frequency operation
- Solder dip 260 °C, 40 s
- · Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

#### **TYPICAL APPLICATIONS**

For use in low voltage, high frequency rectifier of switching mode power supplies, freewheeling diodes, dc-to-dc converters or polarity protection application.

## **MECHANICAL DATA**

Case: TO-247AD (TO-3P)

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per

J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class

1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

<b>MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C unless otherwise noted)								
PARAMETER	SYMBOL	MBR40H35PT	MBR40H45PT	MBR40H50PT	MBR40H60PT	UNIT		
Maximum repetitive peak reverse voltage	V <sub>RRM</sub>	35	45	50	60	V		
Maximum working peak reverse voltage	$V_{RWM}$	35	45	50	60	V		
Maximum DC blocking voltage	$V_{DC}$	35	45	50	60	V		
Maximum average forward rectified current (Fig. 1)	I <sub>F(AV)</sub>	40						
Non-repetitive avalanche energy per diode at 25 °C, $I_{AS} = 4$ A, L = 10 mH	E <sub>AS</sub>	80						
Peak forward surge current, 8.3 ms single half sine-wave superimposed on rated load per diode	I <sub>FSM</sub>	400						
Peak repetitive reverse surge current per diode (1)	I <sub>RRM</sub>	2.0 1.0			Α			
Peak non-repetitive reverse energy (8/20 µs waveform)	E <sub>RSM</sub>	30 25			25	mJ		
Electrostatic discharge capacitor voltage human body model: C = 100 pF, R = 1.5 k $\Omega$	V <sub>C</sub>	25						
Voltage rate of change at (rated V <sub>R</sub> )	dV/dt	10 000						
Operating junction temperature range	T <sub>J</sub>	- 65 to + 175				°C		
Storage temperature range	T <sub>STG</sub>	- 65 to + 175				°C		

#### Note:

(1) 2.0  $\mu$ s pulse width, f = 1.0 kHz

# New Product MBR40H35PT thru MBR40H60PT

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<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise noted)								
PARAMETER	TEST CONDITIONS		SYMBOL		MBR40H35PT MBR40H45PT		MBR40H50PT MBR40H60PT	
				TYP.	MAX.	TYP.	MAX.	
Maximum instantaneous forward voltage per diode <sup>(1)</sup>	I <sub>F</sub> = 20 A I <sub>F</sub> = 20 A I <sub>F</sub> = 40 A I <sub>F</sub> = 40 A	$T_J = 25 ^{\circ}\text{C}$ $T_J = 125 ^{\circ}\text{C}$ $T_J = 25 ^{\circ}\text{C}$ $T_J = 125 ^{\circ}\text{C}$	V <sub>F</sub>	- 0.49 - 0.62	0.63 0.55 0.73 0.66	- 0.56 - 0.68	0.69 0.60 0.83 0.72	>
Maximum reverse current at rated V <sub>R</sub> per diode <sup>(2)</sup>		T <sub>J</sub> = 25 °C T <sub>J</sub> = 125 °C	I <sub>R</sub>	- 9.0	150 25	- 6.0	150 25	μA mA

#### Notes:

(1) Pulse test: 300  $\mu$ s pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

THERMAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted)								
PARAMETER	SYMBOL	MBR40H35PT MBR40H45PT MBR40H50PT MBR40H60PT UN						
Thermal resistance, junction to case per diode	$R_{ heta JC}$	1.2			°C/W			

ORDERING INFORMATION (Example)								
PACKAGE	PREFERRED P/N	D P/N UNIT WEIGHT (g) PACKAGE CODE BASE QUANTITY DELIVERY N						
TO-247AD	MBR40H45PT-E3/45	6.13	45	30/tube	Tube			

## **RATINGS AND CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25 °C unless otherwise noted)

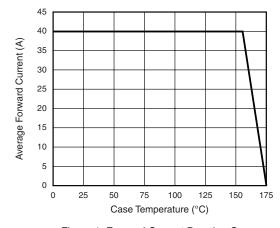


Figure 1. Forward Current Derating Curve

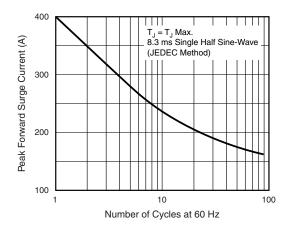


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode



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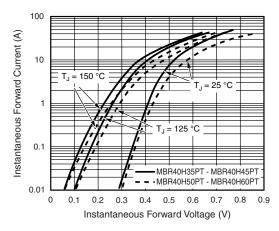


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

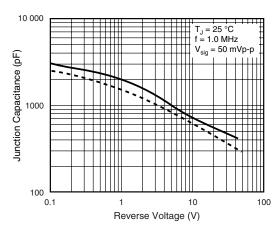


Figure 5. Typical Junction Capacitance Per Diode

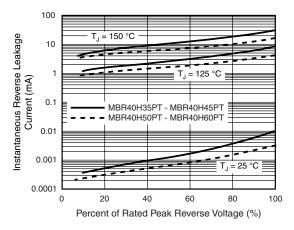


Figure 4. Typical Reverse Characteristics Per Diode

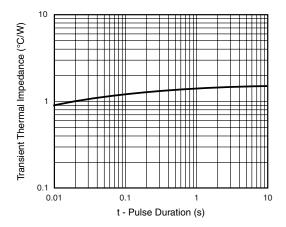
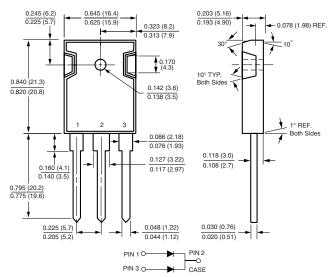


Figure 6. Typical Transient Thermal Impedance Per Diode

## **PACKAGE OUTLINE DIMENSIONS** in inches (millimeters)

## TO-247AD (TO-3P)





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Revision: 18-Jul-08

Document Number: 91000 www.vishay.com